

PUSH-PULL FOUR CHANNEL DRIVER WITH DIODES

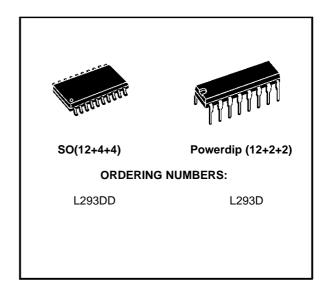
- 600mA OUTPUT CURRENT CAPABILITY PER CHANNEL
- 1.2A PEAK OUTPUT CURRENT (non repetitive) PER CHANNEL
- ENABLE FACILITY
- OVERTEMPERATURE PROTECTION
- LOGICAL "0" INPUT VOLTAGE UP TO 1.5 V (HIGH NOISE IMMUNITY)
- INTERNAL CLAMP DIODES

DESCRIPTION

The Device is a monolithic integrated high voltage, high current four channel driver designed to accept standard DTL or TTL logic levels and drive inductive loads (such as relays solenoides, DC and stepping motors) and switching power transistors.

To simplify use as two bridges each pair of channels is equipped with an enable input. A separate supply input is provided for the logic, allowing operation at a lower voltage and internal clamp diodes are included.

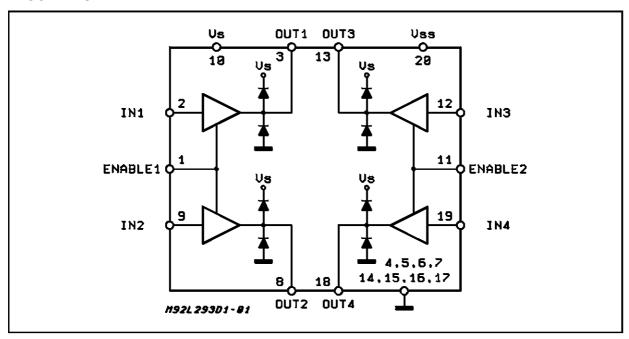
This device is suitable for use in switching applications at frequencies up to 5 kHz.



The L293D is assembled in a 16 lead plastic packaage which has 4 center pins connected together and used for heatsinking

The L293DD is assembled in a 20 lead surface mount which has 8 center pins connected together and used for heatsinking.

BLOCK DIAGRAM

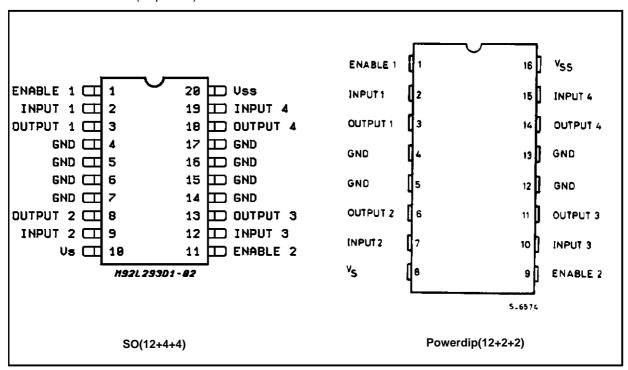


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ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vs	Supply Voltage	36	V
V _{SS}	Logic Supply Voltage	36	V
Vi	Input Voltage	7	V
V _{en}	Enable Voltage	7	V
Io	Peak Output Current (100 μs non repetitive)	1.2	Α
P _{tot}	Total Power Dissipation at T _{pins} = 90 °C	4	W
T_{stg}, T_j	Storage and Junction Temperature	- 40 to 150	°C

PIN CONNECTIONS (Top view)



THERMAL DATA

Symbol	Decription	DIP	SO	Unit
R _{th j-pins}	Thermal Resistance Junction-pins max.	_	14	°C/W
R _{th j-amb}	Thermal Resistance junction-ambient max.	80	50 (*)	°C/W
R _{th j-case}	Thermal Resistance Junction-case max.	14	_	

^(*) With 6sq. cm on board heatsink.



ELECTRICAL CHARACTERISTICS (for each channel, $V_S = 24 \text{ V}$, $V_{SS} = 5 \text{ V}$, $T_{amb} = 25 \,^{\circ}\text{C}$, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Vs	Supply Voltage (pin 10)		V _{SS}		36	V
V_{SS}	Logic Supply Voltage (pin 20)		4.5		36	V
Is	Total Quiescent Supply Current	$V_i = L$; $I_O = 0$; $V_{en} = H$		2	6	mA
	(pin 10)	$V_i = H$; $I_O = 0$; $V_{en} = H$		16	24	mA
		V _{en} = L			4	mA
I _{SS}	Total Quiescent Logic Supply	$V_i = L$; $I_O = 0$; $V_{en} = H$		44	60	mA
	Current (pin 20)	$V_i = H$; $I_O = 0$; $V_{en} = H$		16	22	mA
		V _{en} = L		16	24	mA
V_{IL}	Input Low Voltage (pin 2, 9, 12, 19)		-0.3		1.5	V
V_{IH}	Input High Voltage (pin 2, 9,	V _{SS} ≤ 7 V	2.3		V_{SS}	V
	12, 19)	V _{SS} > 7 V	2.3		7	V
I _{IL}	Low Voltage Input Current (pin 2, 9, 12, 19)	V _{IL} = 1.5 V			- 10	μΑ
Іін	High Voltage Input Current (pin 2, 9, 12, 19)	$2.3 \text{ V} \le \text{V}_{IH} \le \text{V}_{SS} - 0.6 \text{ V}$		30	100	μА
V _{en L}	Enable Low Voltage (pin 1, 11)		-0.3		1.5	V
V _{en H}	Enable High Voltage	V _{SS} ≤ 7 V	2.3		V _{SS}	V
	(pin 1, 11)	V _{SS} > 7 V	2.3		7	V
l _{en L}	Low Voltage Enable Current (pin 1, 11)	V _{en L} = 1.5 V		- 30	- 100	μА
l _{en H}	High Voltage Enable Current (pin 1, 11)	$2.3~\text{V} \leq \text{V}_{\text{en H}} \leq \text{V}_{\text{SS}} - 0.6~\text{V}$			± 10	μА
V _{CE(sat)H}	Source Output Saturation Voltage (pins 3, 8, 13, 18)	I _O = - 0.6 A		1.4	1.8	V
V _{CE(sat)L}	Sink Output Saturation Voltage (pins 3, 8, 13, 18)	I _O = + 0.6 A		1.2	1.8	V
V _F	Clamp Diode Forward Voltage	I _O = 600nA		1.3		V
t _r	Rise Time (*)	0.1 to 0.9 V _O		250		ns
t _f	Fall Time (*)	0.9 to 0.1 V _O		250		ns
t _{on}	Turn-on Delay (*)	0.5 V _i to 0.5 V _O		750		ns
t _{off}	Turn-off Delay (*)	0.5 V _i to 0.5 V _O		200		ns

^(*) See fig. 1.



TRUTH TABLE (one channel)

Input	Enable (*)	Output
Н	Н	Н
L	Н	L
Н	L	Z
L	L	Z

Z = High output impedance

Figure 1: Switching Times

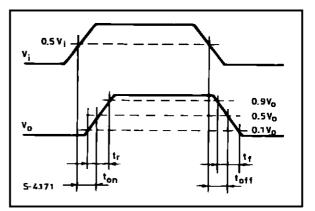
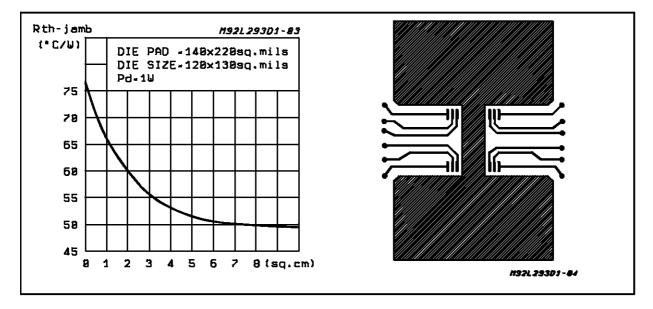


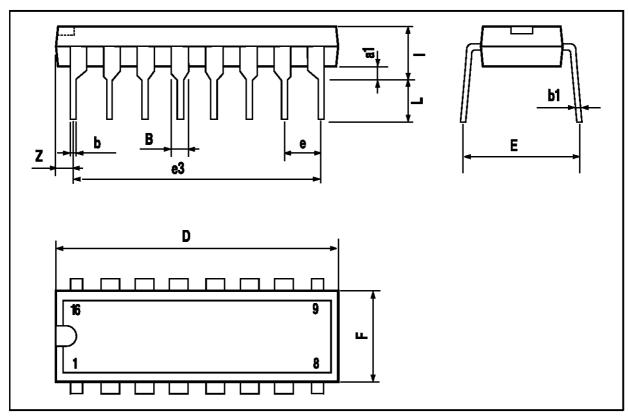
Figure 2: Junction to ambient thermal resistance vs. area on board heatsink (SO12+4+4 package)



^(*) Relative to the considered channel

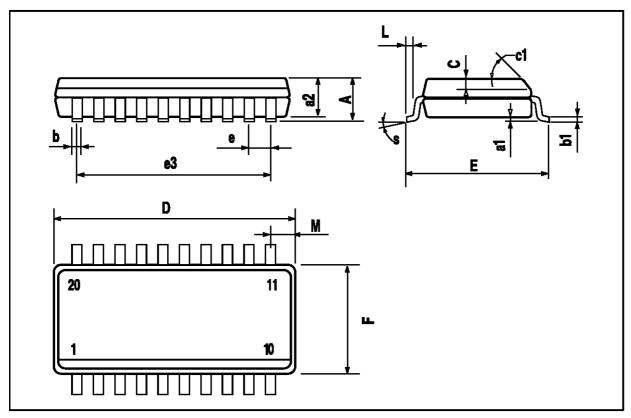
POWERDIP16 PACKAGE MECHANICAL DATA

DIM.		mm		inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	0.85		1.40	0.033		0.055
b		0.50			0.020	
b1	0.38		0.50	0.015		0.020
D			20.0			0.787
E		8.80			0.346	
е		2.54			0.100	
e3		17.78			0.700	
F			7.10			0.280
I			5.10			0.201
L		3.30			0.130	
Z			1.27			0.050



SO20 PACKAGE MECHANICAL DATA

DIM.		mm			inch	
DIWI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α			2.65			0.104
a1	0.1		0.2	0.004		0.008
a2			2.45			0.096
b	0.35		0.49	0.014		0.019
b1	0.23		0.32	0.009		0.013
С		0.5			0.020	
c1		45			1.772	
D		1	12.6		0.039	0.496
E	10		10.65	0.394		0.419
е		1.27			0.050	
e3		11.43			0.450	
F		1	7.4		0.039	0.291
G	8.8		9.15	0.346		0.360
L	0.5		1.27	0.020		0.050
M			0.75			0.030
S	8° (max.)					



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